BUK98150-55A

N-channel TrenchMOS logic level FET

19 March 2014

Product data sheet

1. General description

Logic level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

2. Features and benefits

- Low conduction losses due to low on-state resistance
- Q101 compliant
- Suitable for logic level gate drive sources

3. Applications

- 12 V and 24 V loads
- Automotive and general purpose power switching
- Motors, lamps and solenoids

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 150 °C		-	-	55	V
I _D	drain current	V _{GS} = 5 V; T _{sp} = 25 °C; <u>Fig. 2</u> ; <u>Fig. 3</u>		-	-	5.5	Α
P _{tot}	total power dissipation	T _{sp} = 25 °C; <u>Fig. 1</u>		-	-	8	W
Static charact	eristics						-
R _{DSon}	drain-source on-state	V_{GS} = 4.5 V; I_D = 5 A; T_j = 25 °C		-	-	161	mΩ
	resistance	V _{GS} = 10 V; I _D = 5 A; T _j = 25 °C		-	116	137	mΩ
		$V_{GS} = 5 \text{ V}; I_D = 5 \text{ A}; T_j = 25 ^{\circ}\text{C}; Fig. 12;$ Fig. 13		-	128	150	mΩ
Dynamic char	acteristics						
Q_{GD}	gate-drain charge	$V_{GS} = 5 \text{ V}; I_D = 5 \text{ A}; V_{DS} = 44 \text{ V};$ $T_j = 25 \text{ °C}; Fig. 14$		-	2.8	-	nC
Avalanche rug	Avalanche ruggedness						
E _{DS(AL)S}	non-repetitive drain- source avalanche energy	I_D = 5.5 A; $V_{sup} \le$ 55 V; R_{GS} = 50 Ω; V_{GS} = 5 V; $T_{j(init)}$ = 25 °C; unclamped		-	-	22	mJ



5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	4	D I
2	D	drain		
3	S	source		G T T
4	D	drain	⊟1 ⊟2 ⊟3 SC-73 (SOT223)	mbb076 S

6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
BUK98150-55A	SC-73	plastic surface-mounted package with increased heatsink; 4 leads	SOT223		
BUK98150-55A/CU	SC-73	plastic surface-mounted package with increased heatsink; 4 leads	SOT223		

7. Marking

Table 4. Marking codes

Type number	Marking code
BUK98150-55A	915055A
BUK98150-55A/CU	915055

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 150 °C	-	55	V
V_{DGR}	drain-gate voltage	R_{GS} = 20 k Ω	-	55	V
V_{GS}	gate-source voltage		-15	15	V
P _{tot}	total power dissipation	T _{sp} = 25 °C; <u>Fig. 1</u>	-	8	W
I _D	drain current	$T_{sp} = 25 \text{ °C}; V_{GS} = 5 \text{ V}; Fig. 2; Fig. 3$	-	5.5	Α
		$T_{sp} = 100 ^{\circ}\text{C}; V_{GS} = 5 \text{V}; \frac{\text{Fig. 2}}{\text{C}}$	-	3	Α
I _{DM}	peak drain current	T_{sp} = 25 °C; pulsed; $t_p \le 10 \mu s$; Fig. 3	-	22	Α

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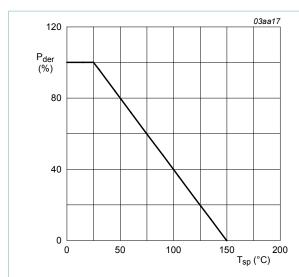
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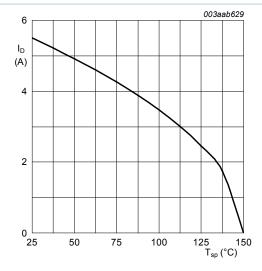
Symbol	Parameter	Conditions		Min	Max	Unit
T _{stg}	storage temperature			-55	150	°C
Tj	junction temperature			-55	150	°C
Source-dra	in diode					
Is	source current	T _{sp} = 25 °C		_	5.5	Α
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{sp} = 25 \ ^{\circ}C$		-	22	Α
Avalanche	ruggedness				-	
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	I_D = 5.5 A; $V_{sup} \le$ 55 V; R_{GS} = 50 Ω; V_{GS} = 5 V; $T_{j(init)}$ = 25 °C; unclamped		-	22	mJ
E _{DS(AL)R}	repetitive drain-source avalanche energy	Fig. 4	[1][2][3]	<u>4]</u>	-	J

- Value not quoted. Repetitive rating defined in avalanche rating figure. Single-pulse avalanche rating limited by maximum junction temperature of 150 $^{\circ}\text{C}.$ [2]
- [3] Repetitive avalanche rating limited by an average junction temperature of 145 °C.
- Refer to application note AN10273 for further information. [4]



Normalized total power dissipation as a function of solder point temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$



Continuous drain current as a function of solder Fig. 2. point temperature

$$V_{GS} \ge 5V$$

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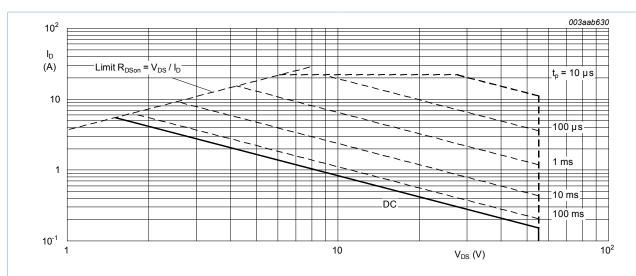


Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

$$T_{mb} = 25 \,^{\circ}C; I_{DM}$$
 is single pulse

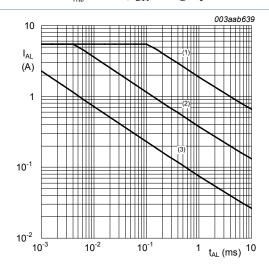


Fig. 4. Single-pulse and repetitive avalanche rating; avalanche current as a function of avalanche time

(1) Single-pulse; $T_j = 25$ °C.

(2) Single-pulse; $T_j = 125 \, ^{\circ}C$.

(3) Repetitive.

9. Thermal characteristics

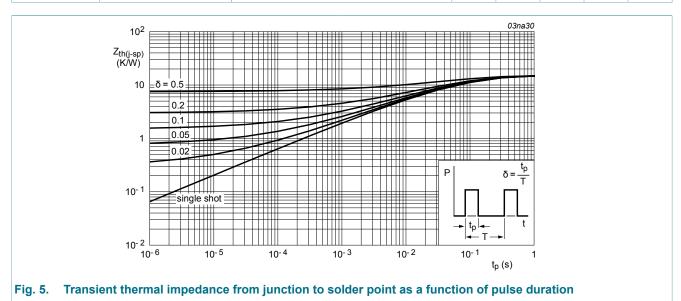
Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-sp)}	thermal resistance from junction to solder point	Fig. 5	-	-	15	K/W

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from junction to ambient		-	120	-	K/W



10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
$V_{(BR)DSS}$	drain-source	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 ^{\circ}\text{C}$	50	-	-	V
	breakdown voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	55	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	I_D = 1 mA; V_{DS} = V_{GS} ; T_j = 25 °C; Fig. 11	1	1.5	2	V
		I_D = 1 mA; V_{DS} = V_{GS} ; T_j = 150 °C; Fig. 11	0.6	-	-	V
		I_D = 1 mA; V_{DS} = V_{GS} ; T_j = -55 °C; Fig. 11	-	-	2.3	V
I _{DSS}	drain leakage current	$V_{DS} = 55 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.05	10	μA
		V _{DS} = 55 V; V _{GS} = 0 V; T _j = 150 °C	-	-	500	μA
I _{GSS}	gate leakage current	V _{GS} = 15 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
		V _{GS} = -15 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
R _{DSon}	drain-source on-state resistance	V _{GS} = 5 V; I _D = 5 A; T _j = 150 °C; Fig. 12; Fig. 13	-	-	276	mΩ
		V _{GS} = 4.5 V; I _D = 5 A; T _j = 25 °C	-	-	161	mΩ
		V _{GS} = 10 V; I _D = 5 A; T _j = 25 °C	-	116	137	mΩ

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		V _{GS} = 5 V; I _D = 5 A; T _j = 25 °C; <u>Fig. 12</u> ; <u>Fig. 13</u>	-	128	150	mΩ
Dynamic cl	haracteristics			'		
Q _{G(tot)}	total gate charge	I _D = 5 A; V _{DS} = 44 V; V _{GS} = 5 V;	-	5.3	-	nC
Q _{GS}	gate-source charge	T _j = 25 °C; <u>Fig. 14</u>	-	1	-	nC
Q _{GD}	gate-drain charge		-	2.8	-	nC
C _{iss}	input capacitance	V _{GS} = 0 V; V _{DS} = 25 V; f = 1 MHz;	-	240	320	pF
C _{oss}	output capacitance	T _j = 25 °C; <u>Fig. 15</u>	-	53	64	pF
C _{rss}	reverse transfer capacitance		-	40	55	pF
t _{d(on)}	turn-on delay time	V_{DS} = 20 V; R_L = 3.3 Ω ; V_{GS} = 5 V;	-	8	-	ns
t _r	rise time	$R_{G(ext)} = 10 \Omega; T_j = 25 ^{\circ}C$	-	57	-	ns
t _{d(off)}	turn-off delay time		-	16	-	ns
t _f	fall time		-	13	-	ns
Source-dra	in diode					
V _{SD}	source-drain voltage	$I_S = 5 \text{ A}$; $V_{GS} = 0 \text{ V}$; $T_j = 25 ^{\circ}\text{C}$; Fig. 16	-	0.85	1.2	V
t _{rr}	reverse recovery time	$I_S = 5 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s};$	-	24	-	ns
Q _r	recovered charge	$V_{GS} = -10 \text{ V}; V_{DS} = 30 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	30	-	nC

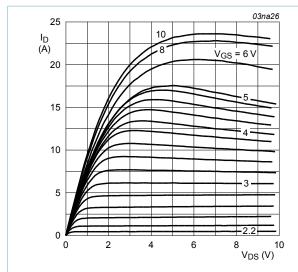


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

$$T_j = 25^{\circ}C; t_p = 300 \mu s$$

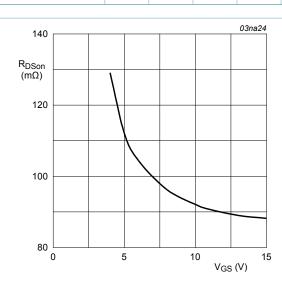


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

$$T_j = 25^{\circ}C; I_D = 5A$$

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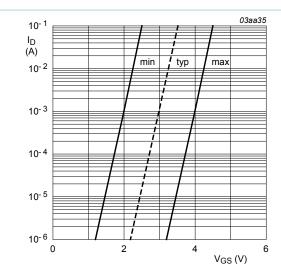


Fig. 8. Sub-threshold drain current as a function of gate-source voltage

$$T_j = 25 \,^{\circ}C; V_{DS} = 5V$$

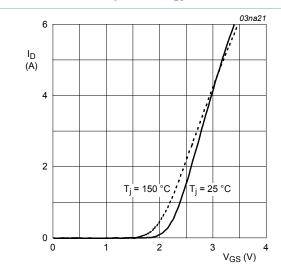


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

$$V_{DS}=25V$$

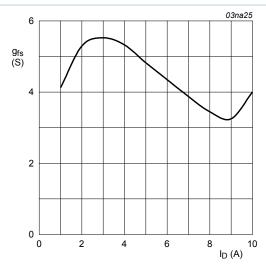


Fig. 9. Forward transconductance as a function of drain current; typical values

$$T_j = 25^{\circ}C; V_{DS} = 25V$$

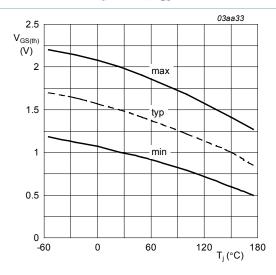


Fig. 11. Gate-source threshold voltage as a function of junction temperature

$$I_D = 1 mA; V_{DS} = V_{GS}$$

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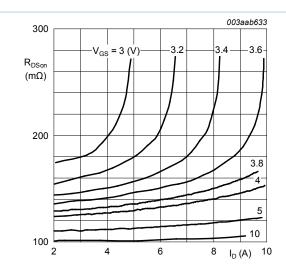


Fig. 12. Drain-source on-state resistance as a function of drain current; typical values

$$T_j = 25$$
° C

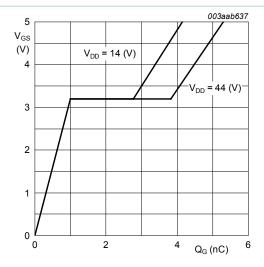


Fig. 14. Gate-source voltage as a function of gate charge; typical values

$$T_j = 25\,^{\circ}C; I_D = 5A$$

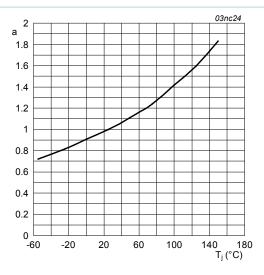


Fig. 13. Normalized drain source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

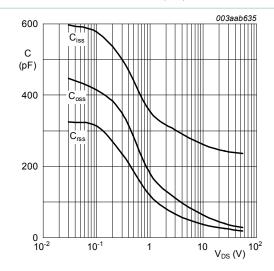


Fig. 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

$$V_{GS} = 0V; f = 1MHz$$

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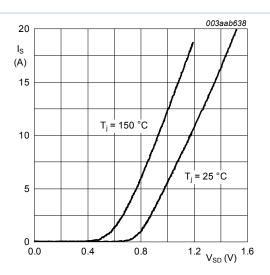


Fig. 16. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

$$V_{GS} = 0 V$$

11. Package outline

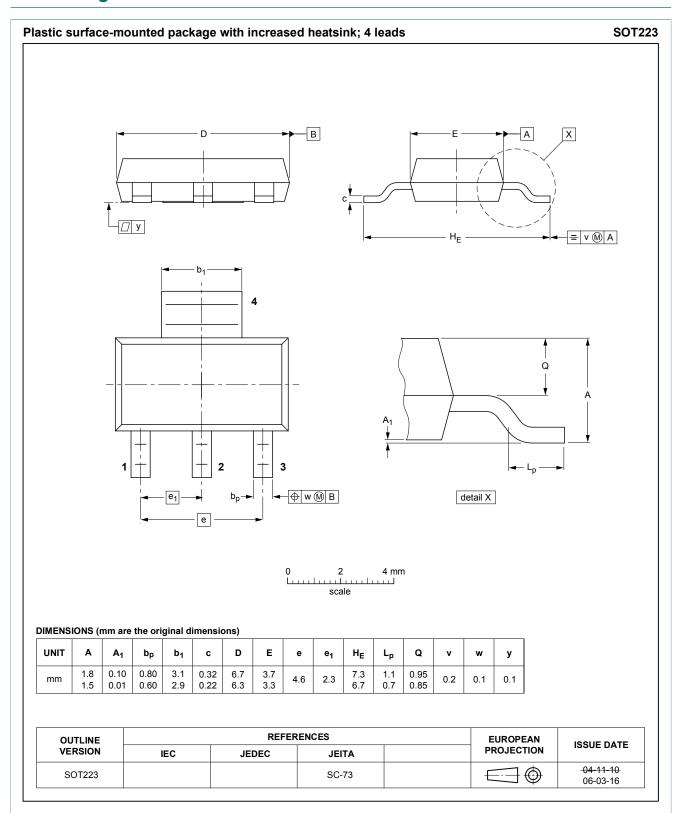


Fig. 17. Package outline SC-73 (SOT223)

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Date of release: 19 March 2014

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